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***PHOTOCATHODE R&D FOR HIGH AVERAGE
CURRENT ERL PHOTOINJECTORS AT
STFC ASTEC***

***B.L. Militsyn on behalf of the ASTeC
photoinjector development team***

*Accelerator Science and Technology Centre
Science & Technology Facility Council, UK*

ERL 2011

the 50th ICFA Advanced Beam Dynamics Workshop
on Energy Recovery Linacs

Outline

- General remarks
- Ultimate demands to high brightness high average current emitters
- Physics of photoemission from high current photocathodes
 - Preparation of the high average current photocathodes
 - Investigation of energy distribution of electrons, emitted from the photocathodes
 - High voltage emittance and response time
 - Operation at high currents, dark and operation lifetime
- Development of the electron injectors for ongoing and future projects:
 - Photocathode design
 - Photocathode transport system
 - ALICE photoinjector upgrade
 - Operation of the ALICE photoinjector (see Tuesday talk)



Production of high average current electron beams

- Emission
 - Thermal emission (medium brightness, difficult controllability)
 - Field emission (high brightness, poor controllability)
 - Photoemission (medium brightness, good controllability)
- Acceleration
 - DC gun (low field, highly stable, acceptable environment for photocathodes, high repetition rate)
 - NC RF guns (high field, medium stability, low repetition rate)
 - SRF guns (medium field, high repetition rate)
- Beam manipulation

Demands on the emitted electron beams for light sources

$$\varepsilon_{n,rms} = \beta\gamma \frac{\lambda}{4\pi}$$

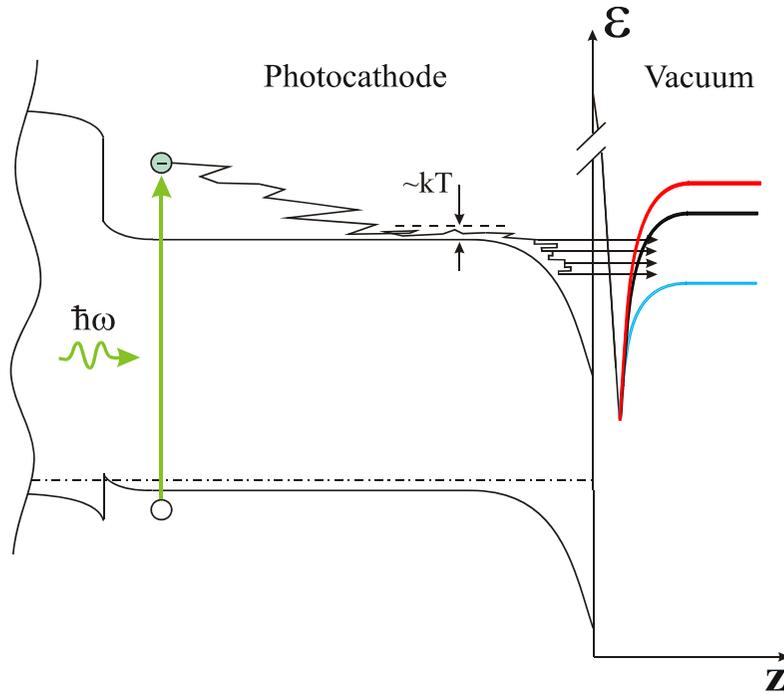
$$\varepsilon_{n,rms} = \sqrt{x^2 x'^2 - x \cdot x'^2} = \sigma_{\perp} \sqrt{\frac{2E_i}{3mc^2}}$$

$$\sigma_{\perp} = \frac{1}{2} \sqrt{\frac{q}{\pi\varepsilon_0 E_c}}$$

$$E_i = 1 \text{ eV}$$

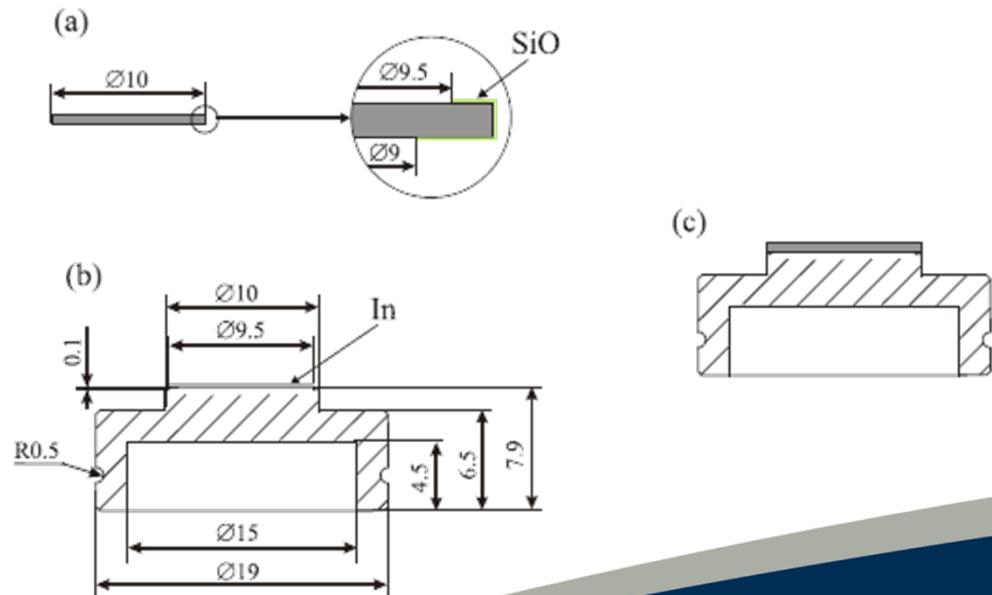
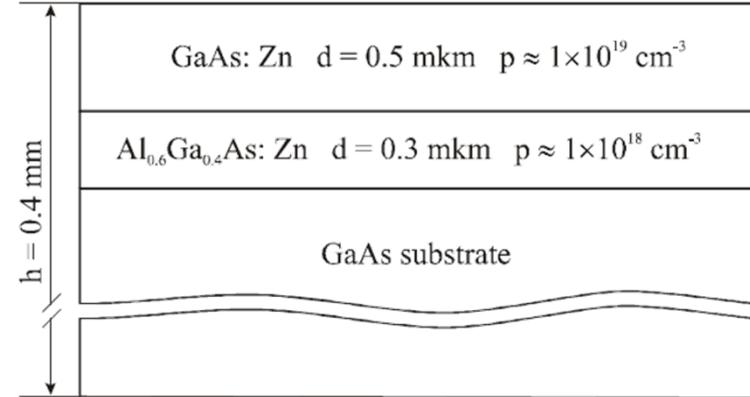
Field strength	Technology	0.01 nC	0.1 nC	1.0 nC
10 MV/m	DC gun	0.11	0.34	1.08
20 MV/m	VHF gun	0.08	0.24	0.77
50 MV/m	L-band gun	0.05	0.15	0.48
100 MV/m	S-band gun	0.03	0.11	0.34

High average current GaAs photocathodes



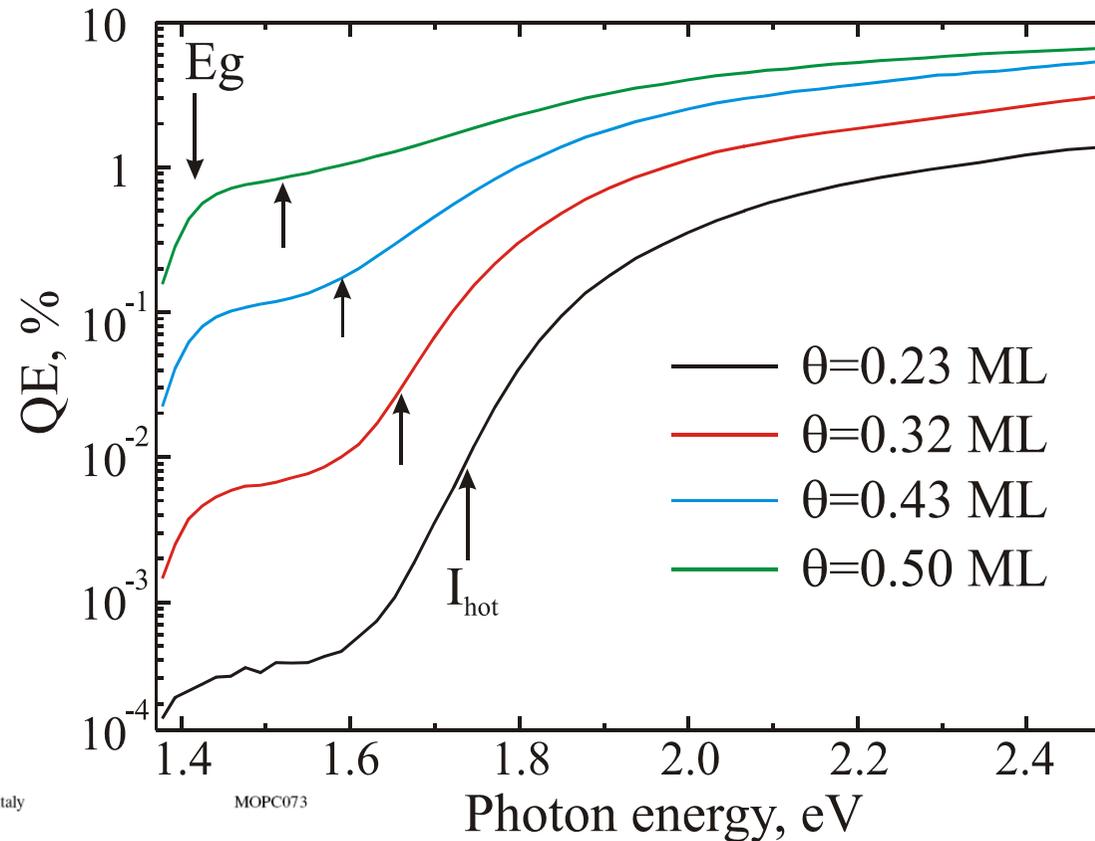
$$\chi > kT \quad E_i = h\nu - E_g - \chi$$

$$\chi < 0 \quad E_i = h\nu - E_g - \chi$$



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GaAs photocathodes. QE and electron affinity



Proceedings of EPAC08, Genoa, Italy

MOPC073

DESIGN OF AN UPGRADE TO THE ALICE PHOTOCATHODE ELECTRON GUN

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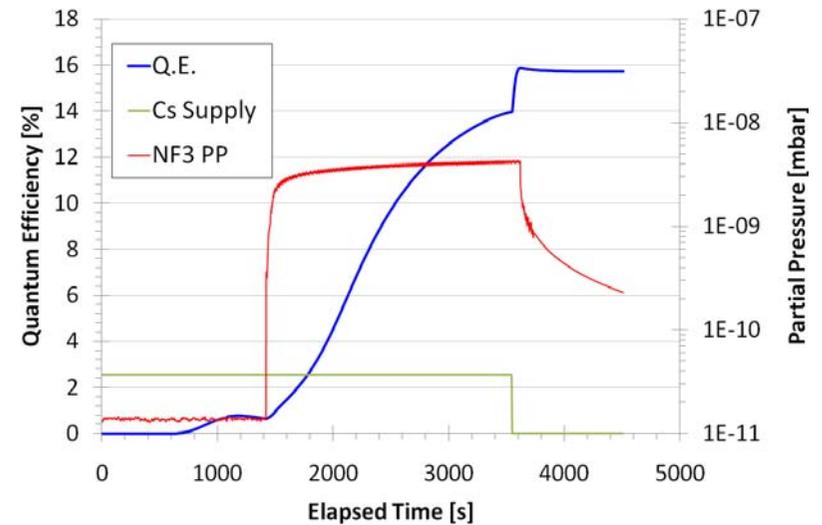
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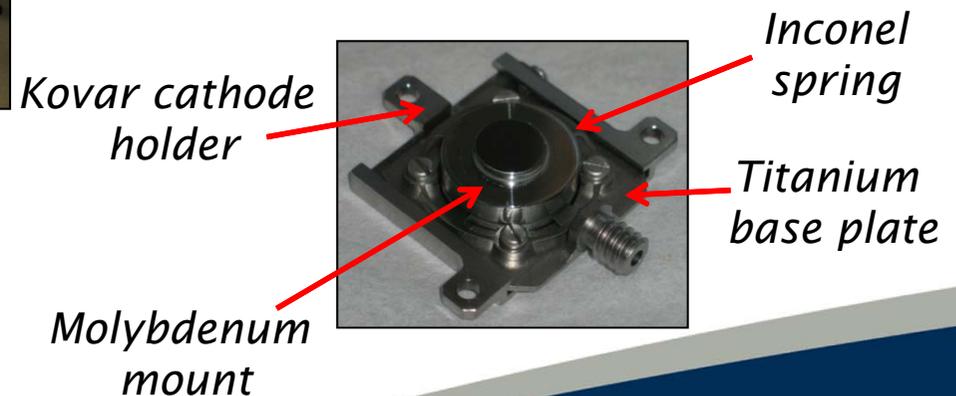
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GaAs photocathode preparation facility



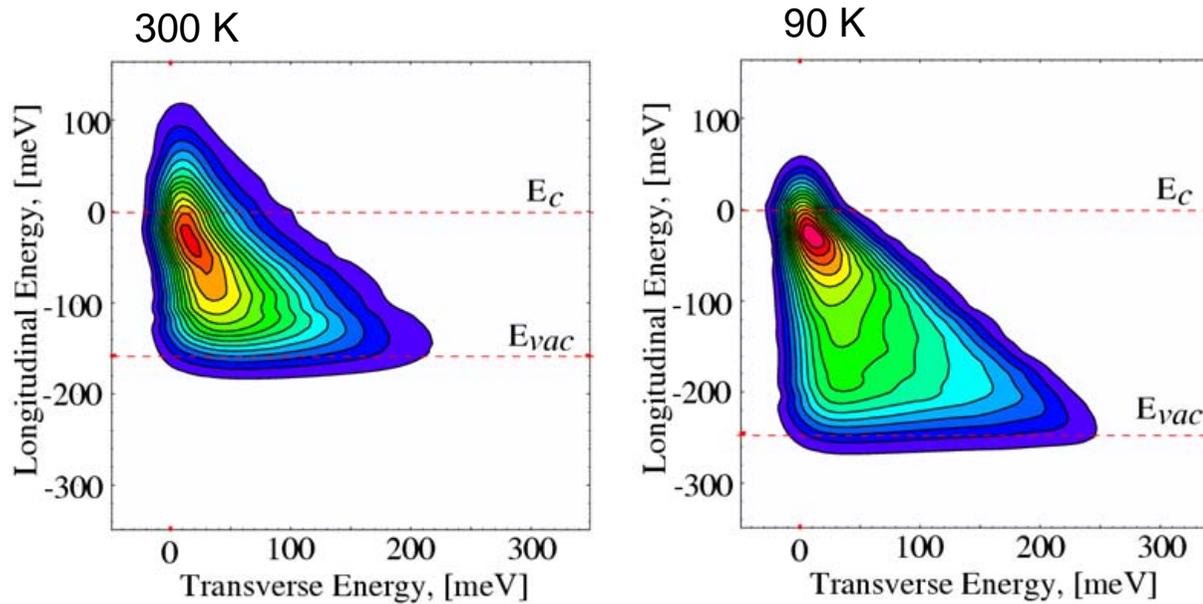
K.J. Middleman et al., PESP2010



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Intrinsic energy of NEA GaAs photocathode

2.5-D energy distributions of emitted photoelectrons



$$E_{\parallel} + E_{\perp} = E_i = \chi$$

D. A. Orlov et al., *Appl. Phys. Lett.* 78 (2001) 2721

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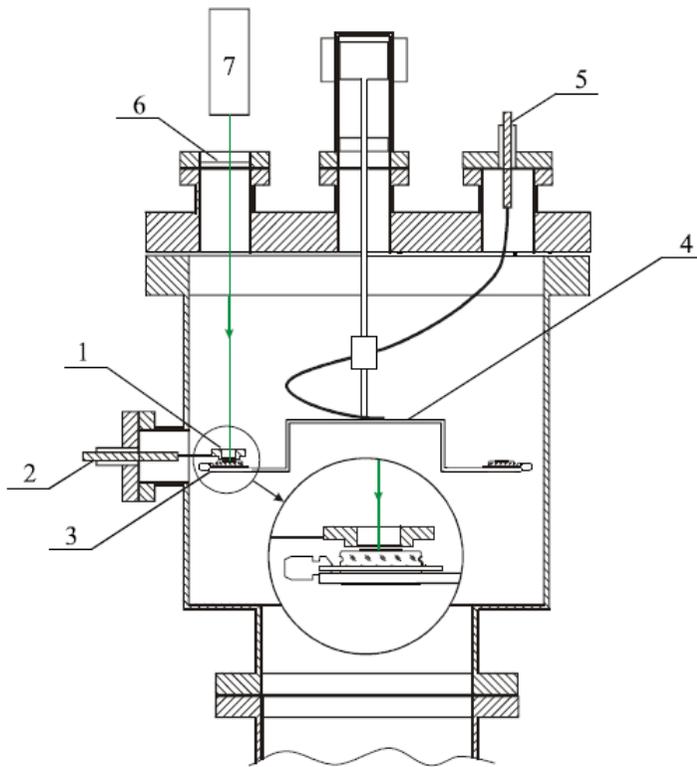
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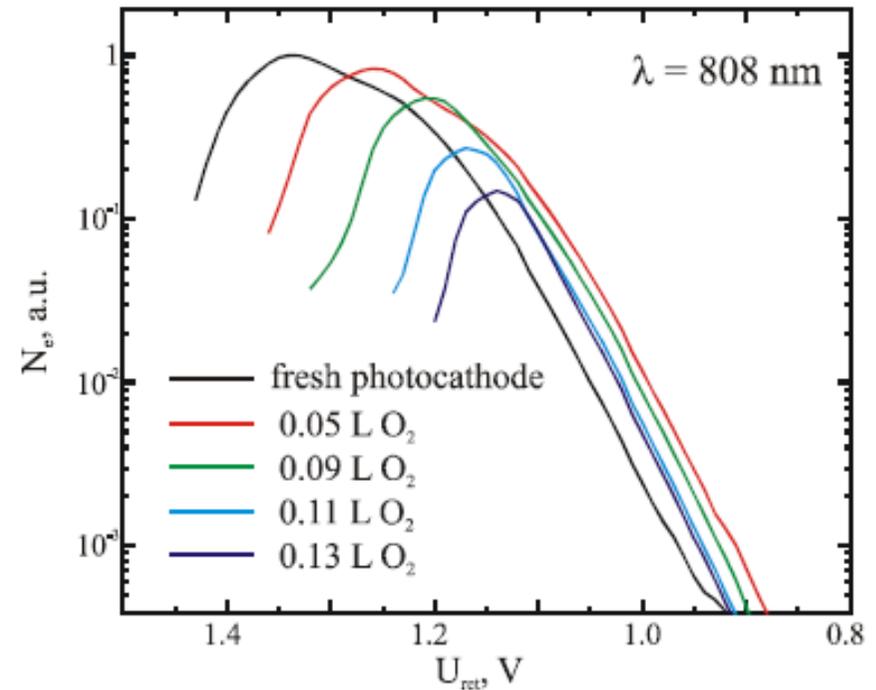
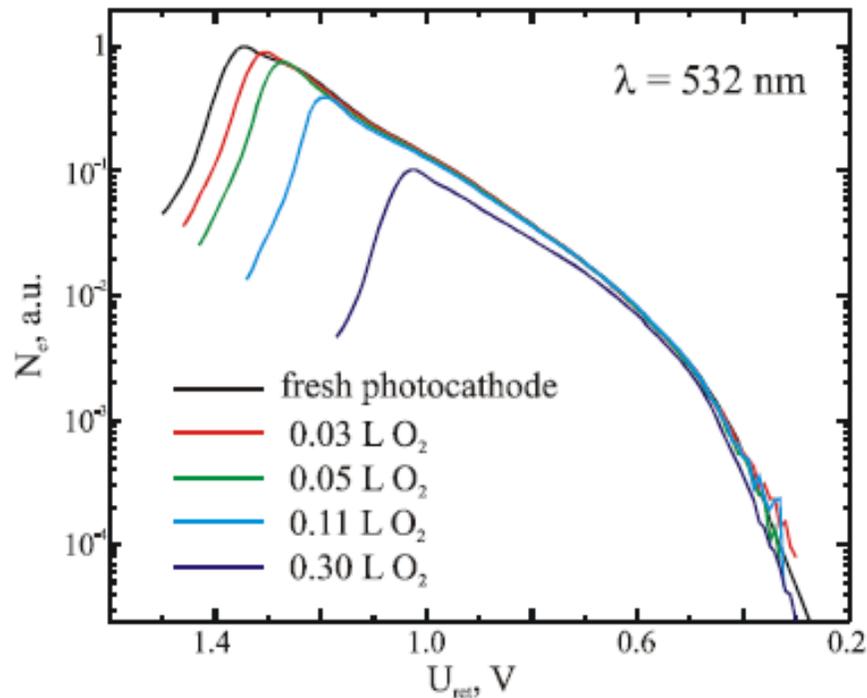
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Intrinsic energy of GaAs photocathodes. longitudinal energy distribution I



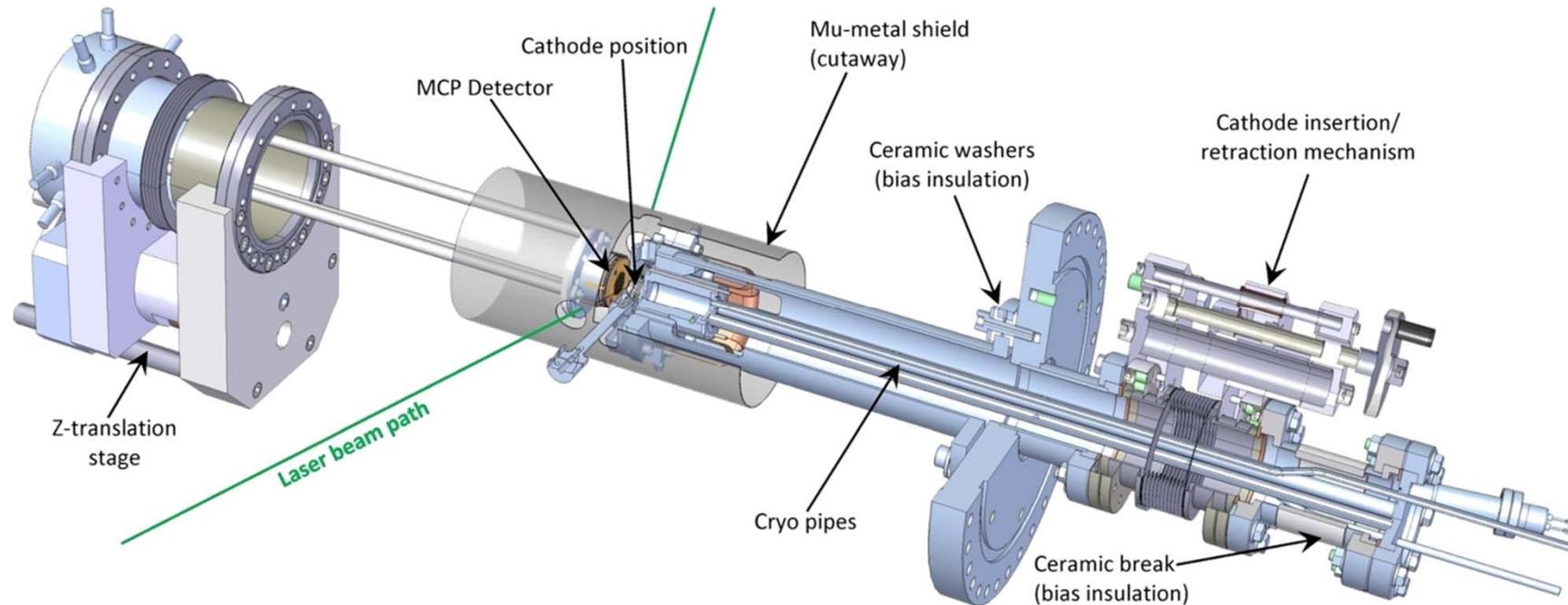
Measurements of the longitudinal energy distribution in a photocathode preparation chamber

Intrinsic energy of GaAs photocathodes. longitudinal energy distribution. Preliminary results



Degradation of the photocathodes with initial QE of 20% at 650 nm

Photocathode energy distribution. 2.5-D energy distribution experiment



Operation at room and LN₂ temperature

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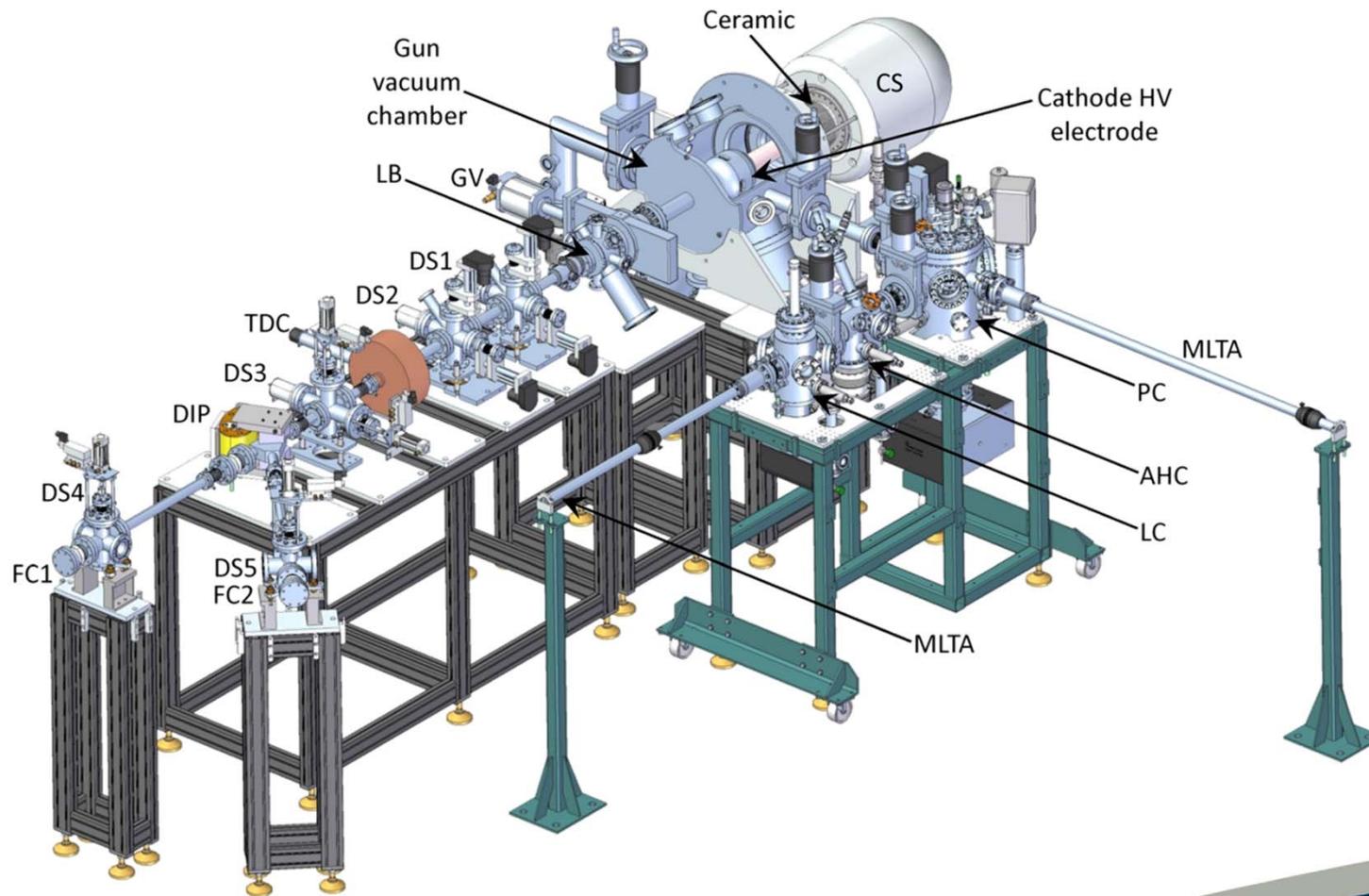
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160 kV research gun for photocathode emittance and response time investigation



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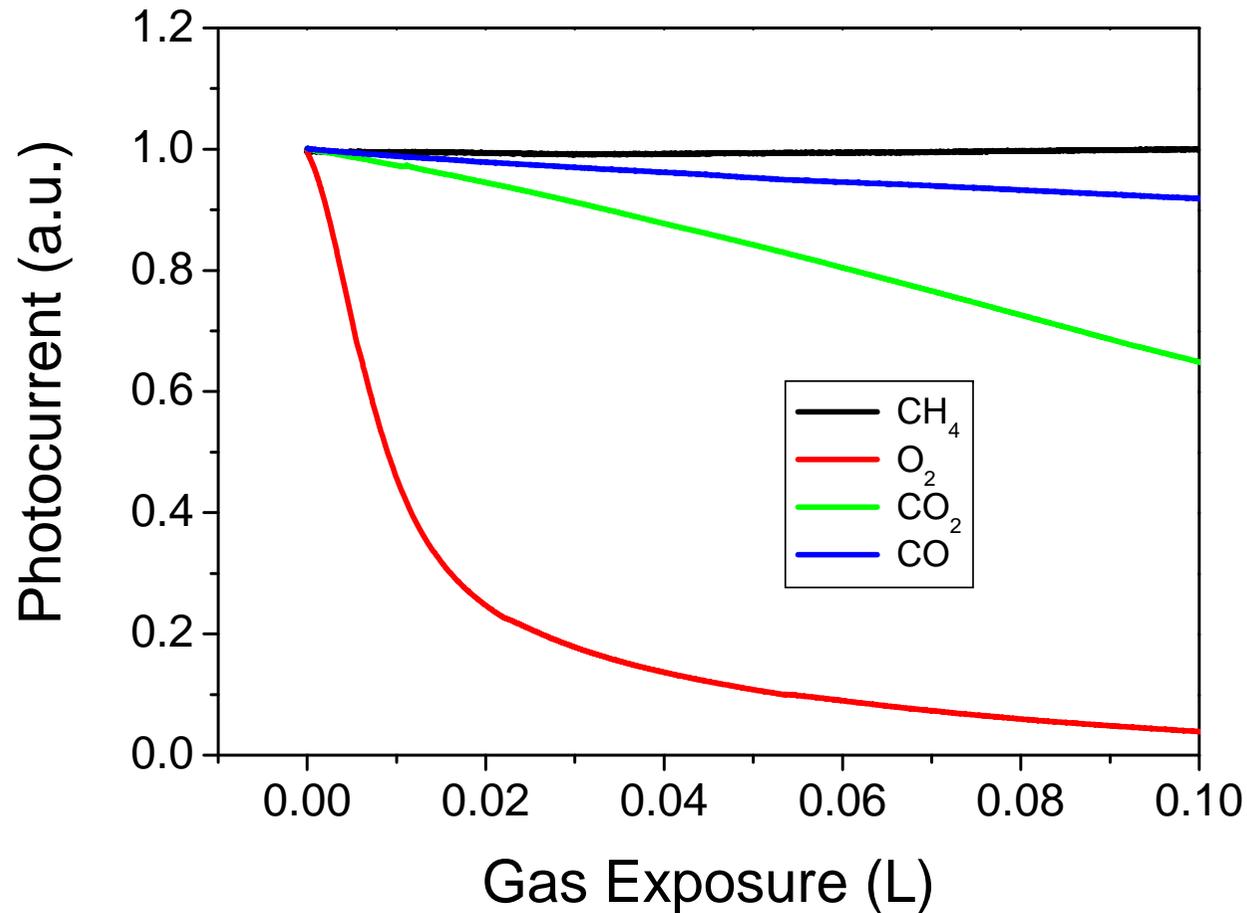
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GaAs photocathodes. Dark life time



K.J. Middleman et al., PESP2010

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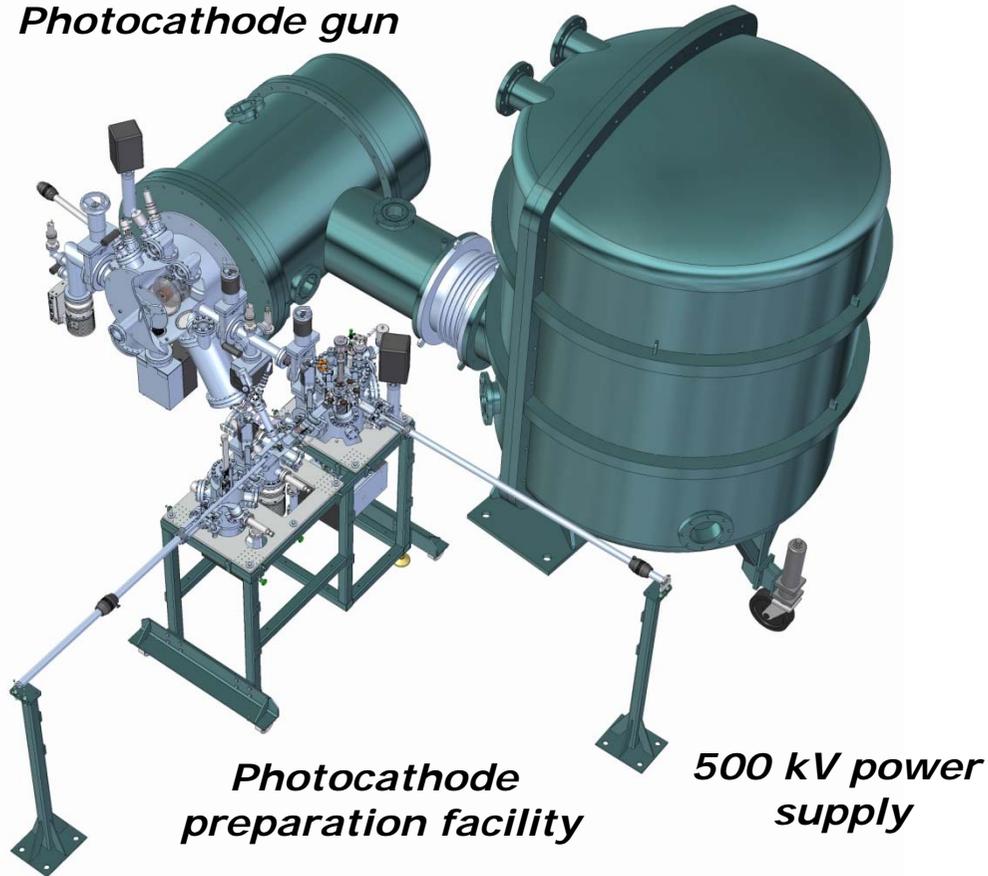


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ALICE DC photocathode gun upgrade

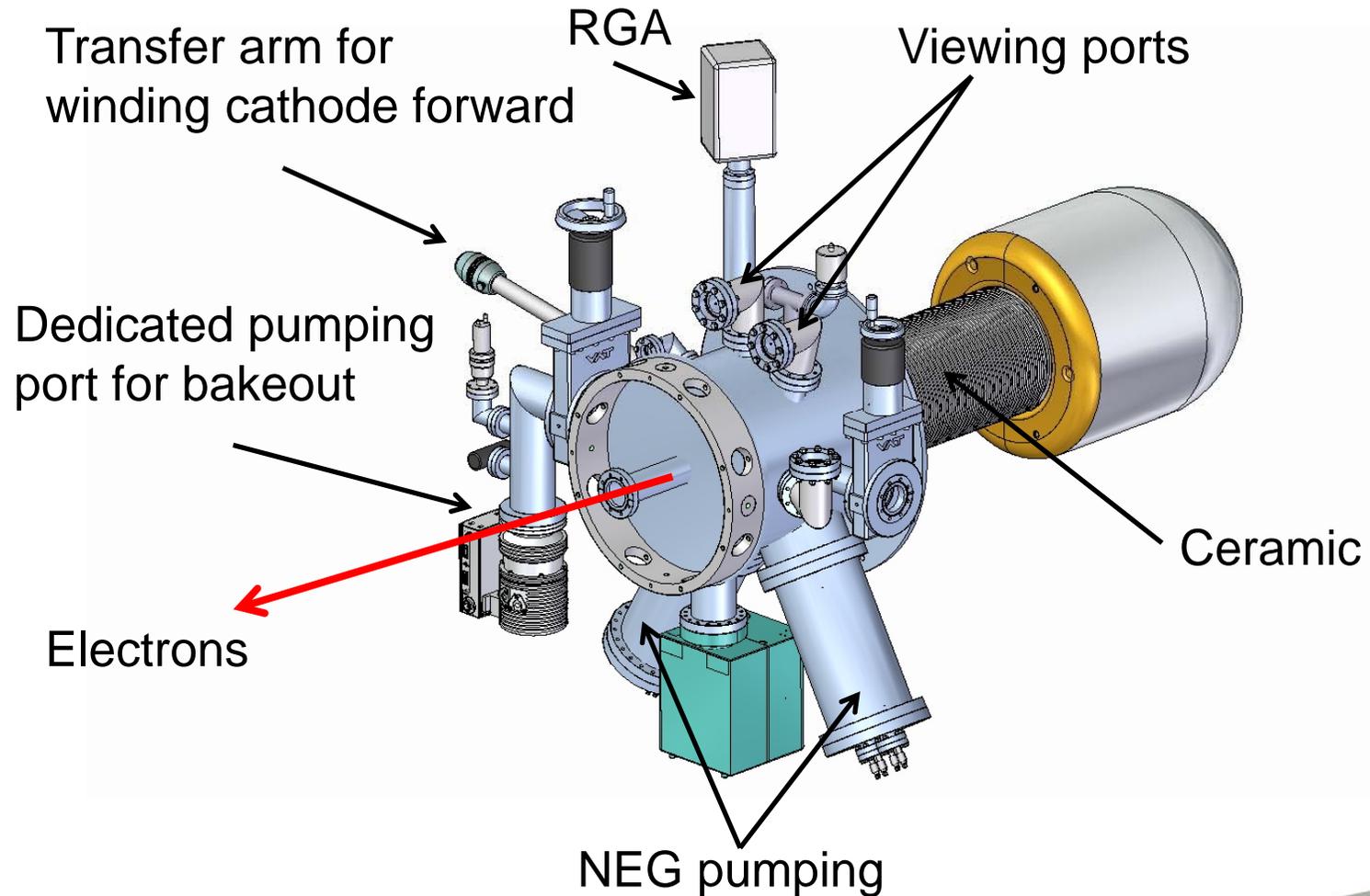
Photocathode gun



Upgrade of the gun allows

- Reduce the down time required for activation of the photocathode and allows ALICE for operation with higher bunch charge.
- Remove activation/caesiation procedure out of the gun
 - Improve vacuum in the gun
 - Reduce contamination of the high voltage electrodes with Cs and other products of photocathode preparation
- Make photocathode activation more controllable
- Allows for experiments with different types of photocathodes

ALICE gun upgrade. New gun chamber



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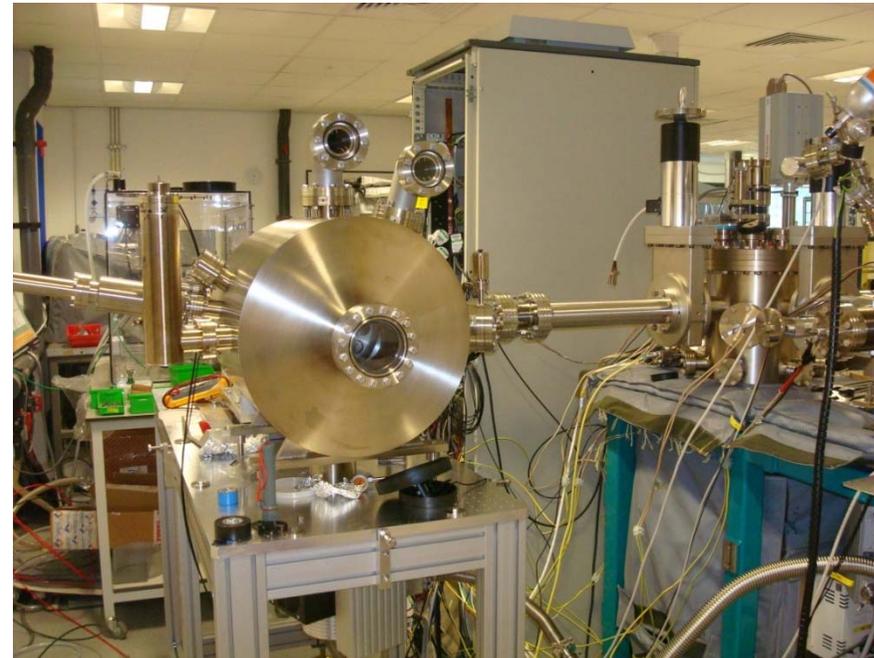
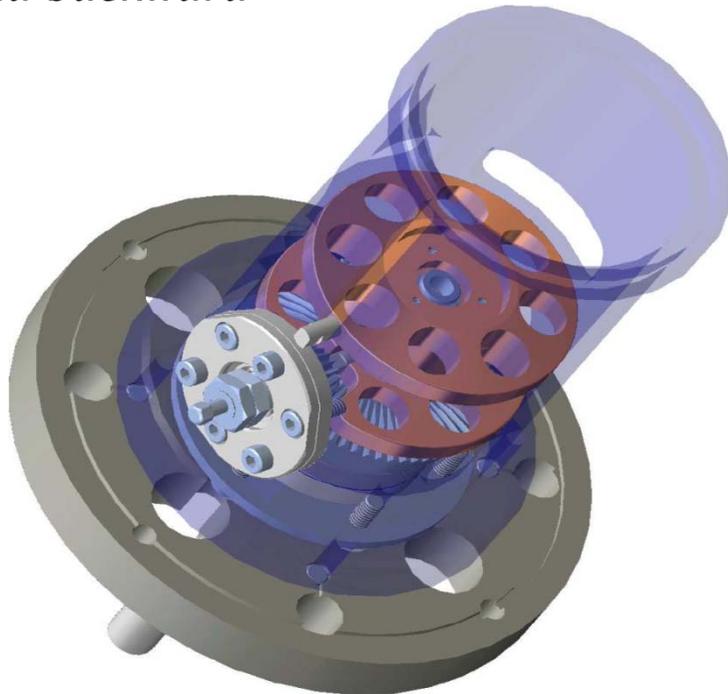


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PPF. Ball Mechanism and Prototype Gun

Cathode ball mechanism based a bevel gear for winding the cathode forward and backward



Mock gun built to test the cathode transfer mechanism. Without bake out the system has worked well

Conclusion

- ASTeC is successfully leading experimental work in the development of high current, high repetition rate photocathodes and photoinjectors
- High current GaAs and GaAsP photocathode technology has been successfully developed and implemented at ASTeC in collaboration with Institute of Semiconductor Physics, Novosibirsk
- Photocathodes designed for 4GLS and ALICE have been manufactured and their activation technology developed to reach quantum efficiencies as high as 20%
- An ALICE gun upgrade utilising GaAs and GaAsP has been designed and manufactured. The gun chamber is now undergoing commissioning
- Further efforts are concentrated on physics of photoemission in particular on investigation of energy spread and time response of III-V photocathodes at both room and cryogenic temperatures



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